imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



MDD200-16N1

Standard Rectifier Module

V_{RRM}	<i>=</i> 2x 1600 V		
I _{FAV}	=	224 A	
V _F	=	1.07 V	

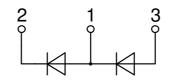
Phase leg

Part number

MDD200-16N1



Backside: isolated **E**72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

MDD200-16N1

Rectifier					Rating	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1700	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1600	V
I _R	reverse current	$V_{R} = 1600 V$	$T_{VJ} = 25^{\circ}C$			1	mA
		$V_{R} = 1600 V$	$T_{vJ} = 150^{\circ}C$			20	mA
V _F	forward voltage drop	I _F = 300 A	$T_{VJ} = 25^{\circ}C$			1.16	V
		I _F = 600 A				1.39	V
		$I_{F} = 300 \text{ A}$	T _{vJ} = 125 °C			1.07	V
		$I_{F} = 600 \text{ A}$				1.36	V
FAV	average forward current	T _c = 100°C	$T_{vJ} = 150 ^{\circ}\text{C}$			224	Α
F(RMS)	RMS forward current	180° sine d = 0.5				350	Α
V _{F0}	threshold voltage		T _{vj} = 150°C			0.80	V
r _F	slope resistance } for power	loss calculation only				0.6	mΩ
R _{thJC}	thermal resistance junction to ca	ase				0.13	K/W
R _{thCH}	thermal resistance case to heats	sink			0.08		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			960	W
	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			10.5	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			11.3	kA
		t = 10 ms; (50 Hz), sine	T _{vj} = 150°C			8.93	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			9.64	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			551.3	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			535.0	kA²s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150^{\circ}C$			398.3	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			386.6	kA²s
C	junction capacitance	V _B = 1100 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		230		pF

MDD200-16N1

Package Y4				Ratings		S		
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					300	Α
T _{vj}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						150		g
M _D	mounting torque				2.25		2.75	Nm
M _T	terminal torque				4.5		5.5	Nm
d _{Spp/App}	creenade distance on surfa	ce striking distance through air	terminal to terminal	14.0	10.0			mm
d _{Spb/Apb}	creepage distance on suna		terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
		t = 1 minute	50/60 Hz, RMS; IIso∟ ≤ 1 mA		3000			V

<u> </u>		<u>L</u>	
Date Code (DC) + Production Index (PI)	DIXYS N yywwAA Part Number Lot.No: xxxxxx	Circuit	1

Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

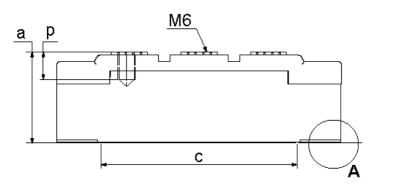
ſ	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MDD200-16N1	MDD200-16N1	Box	6	500212

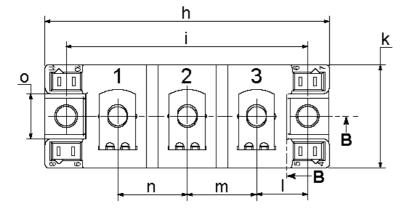
Equiv	alent Circuits for	Simulation	* on die level	T _{vJ} = 150 °C
)- <u>R</u>	Rectifier		
$V_{0 max}$	threshold voltage	0.8		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	0.4		mΩ

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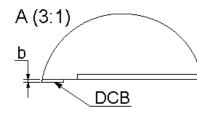
MDD200-16N1

Outlines Y4

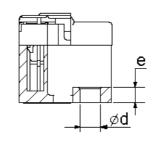


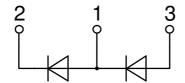


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
а	30.0	30.6	1.181	1.205
b	typ.	0.25	typ. (0.010
с	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
е	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
I	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
0	14.0	15.0	0.551	0.591
р	typ.	10.5	typ. (0.413



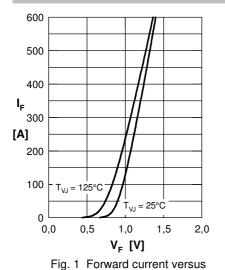






MDD200-16N1

Rectifier



voltage drop

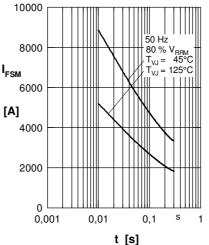


Fig. 2 Surge overload current I_{FSM}: Crest value, t: duration

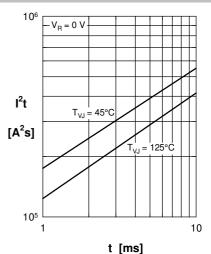


Fig. 3 I²t versus time (1-10 ms)

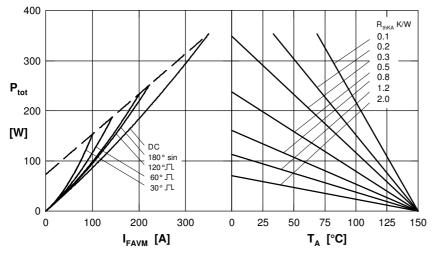
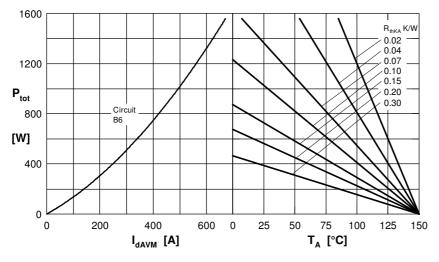
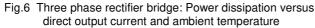


Fig.4 Power dissipation versus forward current and ambient temperature (per diode)





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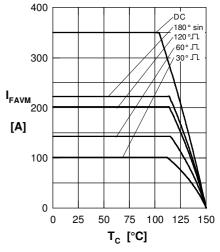


Fig. 5 Maximum forward current at case temperature

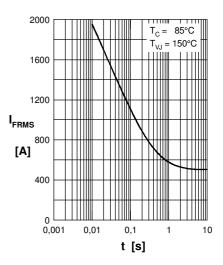


Fig. 7 Rated RMS current versus time (360° conduction)

Rectifier

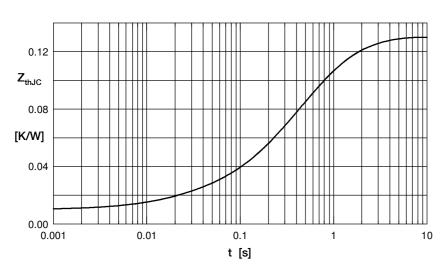


Fig. 8 Transient thermal impedance junction to case

IXYS reserves the right to change limits, conditions and dimensions.

Constants for Z_{th.IC} calculation:

		thJC
i	R _{thi} [K/W]	t _i [s]
1	0.0100	0.00014
2	0.0065	0.019
3	0.0250	0.180
4	0.0615	0.520
5	0.0270	1.600